

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device comprising:
a crystalline semiconductor film-island formed on an insulating surface;
an insulating film formed on the crystalline semiconductor film-island; and
a first signal line and a second signal line, each of which overlaps that partially overlap
the crystalline semiconductor film-island with the insulating film interposed therebetween,
wherein:
the first signal line and the second signal line are connected to each other through a metal
wiring line, and
the metal wiring line at least partially overlaps the crystalline semiconductor island.
2. (Original) A device according to claim 1, wherein the first signal line and the second
signal line are gate signal lines.
3. (Original) A device according to claim 1, wherein the first signal line and the second
signal line are electrically connected to gate electrodes of thin film transistors in a driving circuit
and a pixel region, respectively.
4. (Original) A device according to claim 1, wherein the crystalline semiconductor film
island contains an impurity element giving an n type or a p type conductivity.
5. (Original) A device according to claim 1, wherein the first signal line and the second
signal line are spaced apart from each other so that the first signal line and the crystalline

semiconductor film-island sandwich the insulating film and the second signal line and the crystalline semiconductor film-island sandwich the insulating film, respectively.

6. (Original) A device according to claim 5, wherein the first signal line and the second signal line are gate signal lines.

7. (Original) A device according to claim 5, wherein the first signal line and the second signal line are electrically connected to gate electrodes of thin film transistors in a driving circuit and a pixel region, respectively.

8. (Original) A device according to claim 5, wherein the crystalline semiconductor film island contains an impurity element giving an n type or a p type conductivity.

9. (Original) A device according to claim 1, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

10. (Currently Amended) The [[A]] semiconductor device according to claim 1, the semiconductor device further comprising a pixel region and at least one driving circuit portion, wherein: comprising:

the crystalline semiconductor island, the insulating film, the first signal line, and the second signal line together comprise a first protective circuit; and

the one or more first protective circuit is circuits are provided between the driving circuit and the pixel region, the first protective circuit being connected to each other by a gate signal line,

~~wherein the first protective circuits protect the pixel region and the driving circuit from static electricity.~~

11. (Original) A device according to claim 10, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

12. (Currently Amended) The [[A]] semiconductor device according to claim 10, wherein: comprising a pixel region and at least one driving circuit portion, comprising: the one or more first protective circuit is circuits are provided between a second protective circuit and the pixel region, the first protective circuit being connected to a gate signal line,
~~wherein the first protective circuits protect the pixel region and the second protective circuit from static electricity.~~

13. (Original) A device according to claim 12, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

14. (Withdrawn) A method of manufacturing a semiconductor device comprising:
a first step of forming a crystalline semiconductor film on an insulating surface;
a second step of forming an insulating film on the crystalline semiconductor film;
a third step of forming a conductive film on the insulating film;
a fourth step of patterning the conductive film to form a gate electrode;

a fifth step of forming an interlayer insulating film covering the gate electrode;
a sixth step of forming a contact hole in the interlayer insulating film; and
a seventh step of forming a metal wiring line that is electrically connected to a thin film transistor,

wherein the method further comprises the steps of:

forming a second crystalline semiconductor film on an insulating surface in the first step;

forming an insulating film on the second crystalline semiconductor film in the second step;

patterning the conductive film in the fourth step to form a first gate signal line and a second gate signal line;

forming an interlayer insulating film in the fifth step so as to cover the first gate signal line and the second gate signal line;

forming a contact hole in the interlayer insulating film in the sixth step; and

forming a metal wiring line that electrically connects the first gate signal line with the second gate signal line in the seventh step.

15. (Withdrawn) A method according to claim 14, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

16. (Withdrawn) A method of manufacturing a semiconductor device comprising steps of:

forming first and second crystalline semiconductor films on an insulating surface;
forming an insulating film on the first and second crystalline semiconductor films;
forming a conductive film on the insulating film;

patterning the conductive film to form a gate electrode adjacent to the first semiconductor film and form first and second gate signal lines adjacent to the second semiconductor film;
forming an interlayer insulating film covering the gate electrode and the first and second gate signal lines;
forming a contact hole in the interlayer insulating film; and
forming a metal wiring line that is electrically connected to the first gate signal line with the second gate signal line in the seventh step.

17. (Withdrawn) A method according to claim 16 wherein the first and second gate signal lines are arranged apart from each other over the second semiconductor film.

18. (Withdrawn) A method according to claim 16, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

19-20. (Canceled)

21. (New) A semiconductor device comprising:
a semiconductor island formed over an insulating surface;
a first insulating film formed over the semiconductor island; and
a first signal line and a second signal line, each of which overlaps the semiconductor island with the first insulating film interposed therebetween,
wherein:
the first signal line and the second signal line are connected to each other through a metal wiring line, and
the metal wiring line at least partially overlaps the semiconductor island.

22. (New) A semiconductor device according to claim 21, wherein the semiconductor island comprises a crystalline semiconductor island.

23. (New) A semiconductor device according to claim 22, further comprising a second insulating film formed over the first and second lines, wherein the metal wiring line is formed over the second insulating film.

24. (New) A semiconductor device according to claim 21, further comprising a second insulating film formed over the first and second lines, wherein the metal wiring line is formed over the second insulating film.

25. (New) A semiconductor device comprising:

a first circuit comprising:

a semiconductor island formed over an insulating surface,

a first insulating film formed over the semiconductor island,

a first signal line and a second signal line, each of which overlaps the semiconductor island with the first insulating film interposed therebetween, and

a metal wiring line electrically connecting the first signal line and the second signal line;

a second circuit comprising a transistor; and

a third circuit comprising a transistor;

wherein:

the first signal line is connected to the second circuit and the second signal line is connected to the third circuit, and

the metal wiring line at least partially overlaps the semiconductor island.

26. (New) A semiconductor device according to claim 25, wherein the second circuit is a pixel portion and the third circuit is a driving circuit for driving the pixel portion.

27. (New) A semiconductor device according to claim 25, wherein the second circuit is a pixel portion and the third circuit is a protective circuit.

28. (New) A semiconductor device according to claim 25, wherein the first and second signal lines are gate signal lines.

29. (New) A semiconductor device according to claim 25, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

30. (New) A semiconductor device according to claim 25, further comprising a second insulating film formed over the first and second signal lines, wherein the metal wiring line is formed over the second insulating film.

31. (New) A semiconductor device comprising:

a first circuit comprising:

a first semiconductor island formed over an insulating surface,

a first insulating film formed over the semiconductor island,

a first signal line and a second signal line, each of which overlaps the first semiconductor island with the first insulating film interposed therebetween, and

a first metal wiring line electrically connecting the first signal line and the second signal line;

a second circuit comprising:

a second semiconductor island formed over the insulating surface,
a second insulating film formed over the semiconductor island,
a third signal line and a fourth signal line, each of which overlaps the second
semiconductor island with the second insulating film interposed therebetween, and
a second metal wiring line electrically connecting the third signal line and the
fourth signal line;
a third circuit comprising a transistor; and
a fourth circuit comprising a transistor;
wherein:
the first signal line is connected to the third circuit, the second signal line is connected to
the third signal line, and the fourth signal line is connected to the fourth circuit, and
the first metal wiring line at least partially overlaps the semiconductor island.

32. (New) A semiconductor device according to claim 31, wherein the first and second
metal wiring lines extend in a direction parallel to a direction in which the first and fourth signal
lines extend.

33. (New) A semiconductor device according to claim 31, wherein the first and second
metal wiring lines extend in a direction perpendicular to a direction in which the first and fourth
signal lines extend.

34. (New) A semiconductor device according to claim 31, wherein the third circuit is a
pixel portion and the fourth circuit is a driving circuit for driving the pixel portion.

35. (New) A semiconductor device according to claim 31, wherein the third circuit is a
pixel portion and the fourth circuit is a protective circuit.

36. (New) A semiconductor device according to claim 31, wherein the first and fourth signal lines are gate signal lines.

37. (New) A semiconductor device according to claim 31, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

38. (New) A semiconductor device according to claim 31, further comprising:
a third insulating film formed over the first and second signal lines, and
a fourth insulating film formed over the third and fourth signal lines,
wherein the first metal wiring line is formed over the third insulating film and the second metal wiring line is formed over the fourth insulating film.

39. (New) A semiconductor device comprising:

a first circuit comprising:

 a first semiconductor island formed over an insulating surface,
 a second semiconductor island formed over the insulating surface,
 a first insulating film formed over the first and second semiconductor islands,
 a first signal line that partially overlaps the first semiconductor island with the first insulating film interposed therebetween,
 a second signal line that partially overlaps the second semiconductor island with the first insulating film interposed therebetween,
 a third signal line that partially overlaps the first and second semiconductor islands with the first insulating film interposed therebetween, and
 a metal wiring line electrically connecting the first signal line and the second signal line;

a second circuit comprising a transistor; and

a third circuit comprising a transistor;

wherein:

the first signal line is connected to the second circuit and the second signal line is connected to the third circuit, and

the metal wiring line at least partially overlaps the first and second semiconductor islands.

40. (New) A semiconductor device according to claim 39, wherein the metal wiring line extends in a direction perpendicular to a direction in which the first and second signal lines extend.

41. (New) A semiconductor device according to claim 39, wherein the second circuit is a pixel portion and the third circuit is a driving circuit for driving the pixel portion.

42. (New) A semiconductor device according to claim 39, wherein the second circuit is a pixel portion and the third circuit is a protective circuit.

43. (New) A semiconductor device according to claim 39, wherein the first and second signal lines are gate signal lines.

44. (New) A semiconductor device according to claim 39, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

45. (New) A semiconductor device according to claim 39, further comprising a second insulating film formed over the first and second signal lines, wherein the metal wiring line is formed over the second insulating film.

46. (New) A semiconductor device comprising:

a crystalline semiconductor island formed on an insulating surface;

an insulating film formed on the crystalline semiconductor island; and

a first metal signal line and a second metal signal, each of which overlaps the crystalline semiconductor island with the insulating film interposed therebetween,

wherein the first metal signal line and the second metal signal line are connected to each other through a metal wiring line.

47. (New) A device according to claim 46, wherein the first metal signal line and the second metal signal line are gate signal lines.

48. (New) A device according to claim 46, wherein the first metal signal line and the second metal signal line are electrically connected to gate electrodes of thin film transistors in a driving circuit and a pixel region, respectively.

49. (New) A device according to claim 46, wherein the crystalline semiconductor island contains an impurity element giving an n type or a p type conductivity.

50. (New) A device according to claim 46, wherein the first metal signal line and the second metal signal line are spaced apart from each other so that the first metal signal line and the crystalline semiconductor island sandwich the insulating film and the second metal signal line and the crystalline semiconductor island sandwich the insulating film.

51. (New) A device according to claim 50, wherein the first metal signal line and the second metal signal line are gate signal lines.

52. (New) A device according to claim 50, wherein the first metal signal line and the second metal signal line are electrically connected to gate electrodes of thin film transistors in a driving circuit and a pixel region, respectively.

53. (New) A device according to claim 50, wherein the crystalline semiconductor island contains an impurity element giving an n type or a p type conductivity.

54. (New) A device according to claim 46, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

55. (New) The semiconductor device according to claim 46, the semiconductor device further comprising a pixel region and at least one driving circuit portion, wherein:

the crystalline semiconductor island, the insulating film, the first metal signal line, and the second metal signal line together comprise a first protective circuit; and

the protective circuit is provided between the driving circuit and the pixel region.

56. (New) A device according to claim 55, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

57. (New) The semiconductor device according to claim 55, wherein:
the first protective circuit is provided between a second protective circuit and the pixel
region.

58. (New) A device according to claim 57, wherein said semiconductor device comprises
at least one electric device selected from the group consisting of a video camera, a digital
camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal
computer, a portable information terminal, a mobile computer, a portable telephone and an
electronic book.

59. (New) A semiconductor device comprising:
a semiconductor island formed over an insulating surface;
a first insulating film formed over the semiconductor island; and
a first metal signal line and a second metal signal line, each of which overlaps the
semiconductor island with the first insulating film interposed therebetween,
wherein the first metal signal line and the second metal signal line are connected to each
other through a metal wiring line.

60. (New) A semiconductor device according to claim 59, wherein the semiconductor
island comprises a crystalline semiconductor island.

61. (New) A semiconductor device according to claim 60, further comprising a second
insulating film formed over the first and second metal signal lines, wherein the metal wiring line
is formed over the second insulating film.

62. (New) A semiconductor device according to claim 59, further comprising a second
insulating film formed over the first and second metal signal lines, wherein the metal wiring line
is formed over the second insulating film.

63. (New) A semiconductor device comprising:

a first circuit comprising:

 a semiconductor island formed over an insulating surface,

 a first insulating film formed over the semiconductor island,

 a first metal signal line and a second metal signal line, each of which overlaps the semiconductor island with the first insulating film interposed therebetween, and

 a metal wiring line electrically connecting the first metal signal line and the second metal signal line;

a second circuit comprising a transistor; and

a third circuit comprising a transistor;

wherein the first metal signal line is connected to the second circuit and the second metal signal line is connected to the third circuit.

64. (New) A semiconductor device according to claim 63, wherein the second circuit is a pixel portion and the third circuit is a driving circuit for driving the pixel portion.

65. (New) A semiconductor device according to claim 63, wherein the second circuit is a pixel portion and the third circuit is a protective circuit.

66. (New) A semiconductor device according to claim 63, wherein the first and second metal signal lines are gate signal lines.

67. (New) A semiconductor device according to claim 63, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

68. (New) A semiconductor device according to claim 63, further comprising a second insulating film formed over the first and second metal signal lines, wherein the metal wiring line is formed over the second insulating film.

69. (New) A semiconductor device comprising:

a first circuit comprising:

a first semiconductor island formed over an insulating surface,

a first insulating film formed over the semiconductor island,

a first metal signal line and a second metal signal line, each of which overlaps the first semiconductor island with the first insulating film interposed therebetween, and

a first metal wiring line electrically connecting the first metal signal line and the second metal signal line;

a second circuit comprising:

a second semiconductor island formed over the insulating surface,

a second insulating film formed over the semiconductor island,

a third metal signal line and a fourth metal signal line, each of which overlaps the second semiconductor island with the second insulating film interposed therebetween, and

a second metal wiring line electrically connecting the third metal signal line and the fourth metal signal line;

a third circuit comprising a transistor;

a fourth circuit comprising a transistor;

wherein the first metal signal line is connected to the third circuit, the second metal signal line is connected to the third metal signal line, and the fourth metal signal line is connected to the fourth circuit.

70. (New) A semiconductor device according to claim 69, wherein the first and second metal wiring lines extend in a direction parallel to a direction in which the first and fourth metal signal lines extend.

71. (New) A semiconductor device according to claim 69, wherein the first and second metal wiring lines extend in a direction perpendicular to a direction in which the first and fourth metal signal lines extend.

72. (New) A semiconductor device according to claim 69, wherein the third circuit is a pixel portion and the fourth circuit is a driving circuit for driving the pixel portion.

73. (New) A semiconductor device according to claim 69, wherein the third circuit is a pixel portion and the fourth circuit is a protective circuit.

74. (New) A semiconductor device according to claim 69, wherein the first and fourth metal signal lines are gate signal lines.

75. (New) A semiconductor device according to claim 69, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

76. (New) A semiconductor device according to claim 69, further comprising:
a third insulating film formed over the first and second metal signal lines, and
a fourth insulating film formed over the third and fourth metal signal lines,
wherein the first metal wiring line is formed over the third insulating film and the second metal wiring line is formed over the fourth insulating film.

77. (New) A semiconductor device comprising:

a first circuit comprising:

a first semiconductor island formed over an insulating surface,

a second semiconductor island formed over the insulating surface,

a first insulating film formed over the first and second semiconductor islands,

a first metal signal line that partially overlaps the first semiconductor island with the first insulating film interposed therebetween,

a second metal signal line that partially overlaps the second semiconductor island with the first insulating film interposed therebetween,

a third metal signal line that partially overlaps the first and second semiconductor islands with the first insulating film interposed therebetween, and

a metal wiring line electrically connecting the first metal signal line and the second metal signal line;

a second circuit comprising a transistor; and

a third circuit comprising a transistor;

wherein the first metal signal line is connected to the second circuit and the second metal signal line is connected to the third circuit.

78. (New) A semiconductor device according to claim 77, wherein the metal wiring line extends in a direction perpendicular to a direction in which the first and second metal signal lines extend.

79. (New) A semiconductor device according to claim 77, wherein the second circuit is a pixel portion and the third circuit is a driving circuit for driving the pixel portion.

80. (New) A semiconductor device according to claim 77, wherein the second circuit is a pixel portion and the third circuit is a protective circuit.

81. (New) A semiconductor device according to claim 77, wherein the first and second metal signal lines are gate signal lines.

82. (New) A semiconductor device according to claim 77, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

83. (New) A semiconductor device according to claim 77, further comprising a second insulating film formed over the first and second metal signal lines, wherein the metal wiring line is formed over the second insulating film.

84. (New) A semiconductor device comprising:
a crystalline semiconductor island formed on an insulating surface;
an insulating film formed on the crystalline semiconductor island; and
a first signal line and a second signal, each of which overlaps the crystalline semiconductor island with the insulating film interposed therebetween,

wherein:

the first signal line and the second signal line are connected to each other through a metal wiring line, and

the crystalline semiconductor island is interposed between the first signal line and the second signal line.

85. (New) A device according to claim 84, wherein the first signal line and the second signal line are gate signal lines.

86. (New) A device according to claim 84, wherein the first signal line and the second signal line are electrically connected to gate electrodes of thin film transistors in a driving circuit and a pixel region, respectively.

87. (New) A device according to claim 84, wherein the crystalline semiconductor island contains an impurity element giving an n type or a p type conductivity.

88. (New) A device according to claim 84, wherein the first signal line and the second signal line are spaced apart from each other so that the first signal line and the crystalline semiconductor island sandwich the insulating film and the second signal line and the crystalline semiconductor island sandwich the insulating film, respectively.

89. (New) A device according to claim 88, wherein the first signal line and the second signal line are gate signal lines.

90. (New) A device according to claim 88, wherein the first signal line and the second signal line are electrically connected to gate electrodes of thin film transistors in a driving circuit and a pixel region, respectively.

91. (New) A device according to claim 88, wherein the crystalline semiconductor island contains an impurity element giving an n type or a p type conductivity.

92. (New) A device according to claim 84, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

93. (New) The semiconductor device according to claim 84, the semiconductor device further comprising a pixel region and at least one driving circuit portion, wherein:

the crystalline semiconductor island, the insulating film, the first signal line, and the second signal line together comprise a first protective circuit; and

the protective circuit is provided between the driving circuit and the pixel region.

94. (New) A device according to claim 93, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

95. (New) The semiconductor device according to claim 93, wherein:

the first protective circuit is provided between a second protective circuit and the pixel region.

96. (New) A device according to claim 95, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

97. (New) A semiconductor device comprising:

a semiconductor island formed over an insulating surface;

a first insulating film formed over the semiconductor island; and

a first signal line and a second signal line, each of which overlaps the semiconductor island with the first insulating film interposed therebetween,

wherein:

the first signal line and the second signal line are connected to each other through a metal wiring line, and

the semiconductor island is interposed between the first signal line and the second signal line.

98. (New) A semiconductor device according to claim 97, wherein the semiconductor island comprises a crystalline semiconductor island.

99. (New) A semiconductor device according to claim 98, further comprising a second insulating film formed over the first and second lines, wherein the metal wiring line is formed over the second insulating film.

100. (New) A semiconductor device according to claim 97, further comprising a second insulating film formed over the first and second lines, wherein the metal wiring line is formed over the second insulating film.

101. (New) A semiconductor device comprising:

a first circuit comprising:

a semiconductor island formed over an insulating surface,

a first insulating film formed over the semiconductor island,

a first signal line and a second signal line, each of which overlaps the semiconductor island with the first insulating film interposed therebetween, and

a metal wiring line electrically connecting the first signal line and the second signal line;

a second circuit comprising a transistor; and

a third circuit comprising a transistor;

wherein:

the first signal line is connected to the second circuit and the second signal line is connected to the third circuit, and

the semiconductor island is interposed between the first signal line and the second signal line.

102. (New) A semiconductor device according to claim 101, wherein the second circuit is a pixel portion and the third circuit is a driving circuit for driving the pixel portion.

103. (New) A semiconductor device according to claim 101, wherein the second circuit is a pixel portion and the third circuit is a protective circuit.

104. (New) A semiconductor device according to claim 101, wherein the first and second signal lines are gate signal lines.

105. (New) A semiconductor device according to claim 101, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

106. (New) A semiconductor device according to claim 101, further comprising a second insulating film formed over the first and second signal lines, wherein the metal wiring line is formed over the second insulating film.

107. (New) A semiconductor device comprising:

a first circuit comprising:

 a first semiconductor island formed over an insulating surface,

 a first insulating film formed over the semiconductor island,

a first signal line and a second signal line, each of which overlaps the first semiconductor island with the first insulating film interposed therebetween, and
a first metal wiring line electrically connecting the first signal line and the second signal line;
a second circuit comprising:
a second semiconductor island formed over the insulating surface,
a second insulating film formed over the semiconductor island,
a third signal line and a fourth signal line, each of which overlaps the second semiconductor island with the second insulating film interposed therebetween, and
a second metal wiring line electrically connecting the third signal line and the fourth signal line;
a third circuit comprising a transistor;
a fourth circuit comprising a transistor;
wherein:
the first signal line is connected to the third circuit, the second signal line is connected to the third signal line, and the fourth signal line is connected to the fourth circuit, and
the first semiconductor island is interposed between the first signal line and the second signal line.

108. (New) A semiconductor device according to claim 107, wherein the first and second metal wiring lines extend in a direction parallel to a direction in which the first and fourth signal lines extend.

109. (New) A semiconductor device according to claim 107, wherein the first and second metal wiring lines extend in a direction perpendicular to a direction in which the first and fourth signal lines extend.

110. (New) A semiconductor device according to claim 107, wherein the third circuit is a pixel portion and the fourth circuit is a driving circuit for driving the pixel portion.

111. (New) A semiconductor device according to claim 107, wherein the third circuit is a pixel portion and the fourth circuit is a protective circuit.

112. (New) A semiconductor device according to claim 107, wherein the first and fourth signal lines are gate signal lines.

113. (New) A semiconductor device according to claim 107, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

114. (New) A semiconductor device according to claim 107, further comprising:
a third insulating film formed over the first and second signal lines, and
a fourth insulating film formed over the third and fourth signal lines,
wherein the first metal wiring line is formed over the third insulating film and the second metal wiring line is formed over the fourth insulating film.

115. (New) A semiconductor device comprising:
a first circuit comprising:

 a first semiconductor island formed over an insulating surface,
 a second semiconductor island formed over the insulating surface,
 a first insulating film formed over the first and second semiconductor islands,
 a first signal line that partially overlaps the first semiconductor island with the first insulating film interposed therebetween,

a second signal line that partially overlaps the second semiconductor island with the first insulating film interposed therebetween,

a third signal line that partially overlaps the first and second semiconductor islands with the first insulating film interposed therebetween, and

a metal wiring line electrically connecting the first signal line and the second signal line;

a second circuit comprising a transistor; and

a third circuit comprising a transistor;

wherein:

the first signal line is connected to the second circuit and the second signal line is connected to the third circuit, and

the first and second semiconductor islands are interposed between the first signal line and the second signal line.

116. (New) A semiconductor device according to claim 115, wherein the metal wiring line extends in a direction perpendicular to a direction in which the first and second signal lines extend.

117. (New) A semiconductor device according to claim 115, wherein the second circuit is a pixel portion and the third circuit is a driving circuit for driving the pixel portion.

118. (New) A semiconductor device according to claim 115, wherein the second circuit is a pixel portion and the third circuit is a protective circuit.

119. (New) A semiconductor device according to claim 115, wherein the first and second signal lines are gate signal lines.

120. (New) A semiconductor device according to claim 115, wherein said semiconductor device comprises at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, a portable information terminal, a mobile computer, a portable telephone and an electronic book.

121. (New) A semiconductor device according to claim 115, further comprising a second insulating film formed over the first and second signal lines, wherein the metal wiring line is formed over the second insulating film.